

# MPSW56



# **PNP General Purpose Amplifier**

This device is designed for general purpose medium power amplifiers and switches requiring collector currents to 800 mA. Sourced from Process 79.

# **Absolute Maximum Ratings\***

TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
$V_{CEO}$	Collector-Emitter Voltage	80	V
$V_{CBO}$	Collector-Base Voltage	80	V
$V_{EBO}$	Emitter-Base Voltage	4.0	V
I <sub>C</sub>	Collector Current - Continuous 1.		A
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

1) These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

### **Thermal Characteristics**

TA = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units
		MPSW56	
P <sub>D</sub>	Total Device Dissipation	1.0	W
	Derate above 25°C	8.0	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	50	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	125	°C/W

<sup>\*</sup>Device mounted on FR-4 PCB 36 mm X 18 mm X 1.5 mm; mounting pad for the collector lead min. 6 cm<sup>2</sup>.

# **PNP General Purpose Amplifier**

Max

Min

(continued)

Units

Elect	rical	Ch	ara	cter	isti	ics

**Parameter** 

Symbol

TA = 25°C unless otherwise noted

**Test Conditions** 

OFF CHA	ARACTERISTICS				
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 1.0 m A, I <sub>B</sub> = 0	80		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 100 μA, I <sub>E</sub> = 0	80		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1.0 m A, I <sub>C</sub> = 0	4.0		V
Ісво	Collector-Cutoff Current	V <sub>CB</sub> = 60 V, I <sub>E</sub> = 0		0.1	μΑ
I <sub>CEO</sub>	Collector-Cutoff Current	V <sub>CE</sub> = 60 V		0.5	μΑ
I <sub>EBO</sub>	Emitter-Cutoff Current	V <sub>EB</sub> = 3.0 V, I <sub>C</sub> = 0		0.10	μΑ

### ON CHARACTERISTICS\*

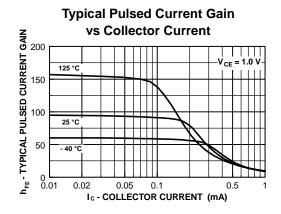
h <sub>FE</sub>	DC Current Gain	$I_C = 50 \text{ mA}, V_{CE} = 1.0 \text{ V}$	100		
		$I_C = 250 \text{ mA}, V_{CE} = 1.0 \text{ V}$	50		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$I_C = 250 \text{ mA}, I_B = 10 \text{ mA}$		0.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	$I_C = 250 \text{ mA}, V_{CE} = 5.0 \text{ V}$		1.2	V

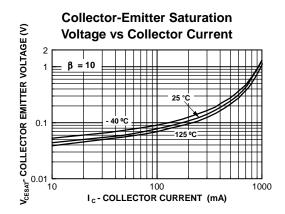
### SMALL SIGNAL CHARACTERISTICS

f <sub>T</sub>	Current Gain-Bandwidth Product	$I_C = 250 \text{ mA}, V_{CE} = 5.0 \text{ V},$	50		MHz
		f = 20 MHz			
C <sub>ob</sub>	Collector-Base Capacitance	$V_{CB} = 10 \text{ V}, I_{E} = 0, f = 1.0 \text{ MHz}$		15	pF

<sup>\*</sup>Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  1.0%

# **Typical Characteristics**

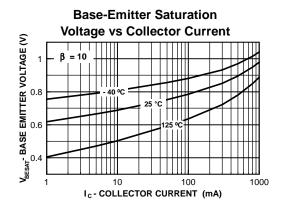


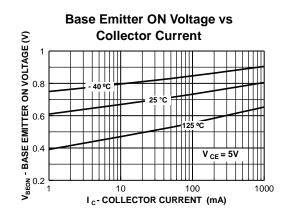


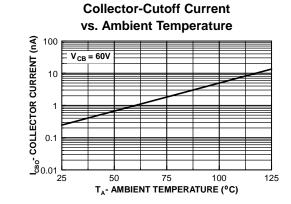
# **PNP General Purpose Amplifier**

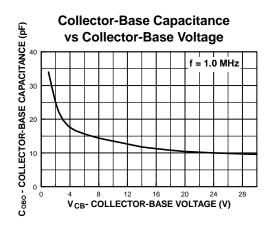
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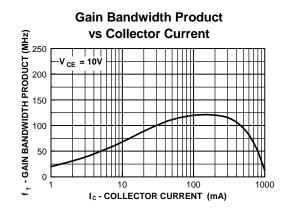
# Typical Characteristics (continued)

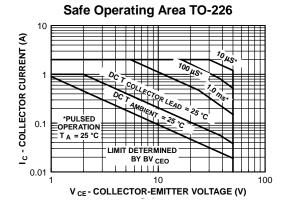






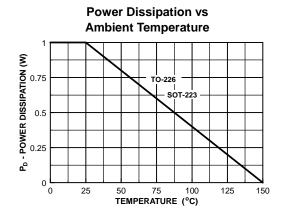






# PNP General Purpose Amplifier (continued)

# Typical Characteristics (continued)



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